

# **Dual Channel Small Outline Optoisolators**

## **Transistor Output (Low Input Current)**

The MOCD217 device consists of two gallium arsenide infrared emitting diodes optically coupled to two monolithic silicon phototransistor detectors, in a surface mountable, small outline, plastic package. It is ideally suited for high density applications and eliminates the need for through–the–board mounting.

- · Dual Channel Coupler
- Convenient Plastic SOIC-8 Surface Mountable Package Style
- Low Input Current (Specified @ 1 mA)
- Minimum V(BR)CEO of 30 Volts Guaranteed
- Standard SOIC–8 Footprint, with 0.050" Lead Spacing
- Shipped in Tape and Reel, which conforms to EIA Standard RS481A
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- High Input-Output Isolation of 3000 Vac (rms) Guaranteed
- Meets U.L. Regulatory Requirements, File #E90700, Volume 2

#### **Ordering Information:**

- To obtain MOCD217 in tape and reel, add R2 suffix to device number as follows:
   R2 = 2500 units on 13" reel
- To obtain MOCD217 in quantities of 50 (shipped in sleeves) no suffix

#### **Marking Information:**

MOCD217 = D217

## MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted) Rating

Forward Current — Continuous	lF	60	mA
Forward Current — Peak (PW = 100 $\mu$ s, 120 pps)	I <sub>F</sub> (pk)	1.0	А
Reverse Voltage	$V_{R}$	6.0	V
LED Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	90 0.8	mW mW/°C
OUTPUT TRANSISTOR			
Collector–Emitter Voltage	VCEO	30	V
Collector-Base Voltage	V <sub>CBO</sub>	70	V
Emitter–Collector Voltage	VECO	7.0	V
Collector Current — Continuous	IC	150	mA
Detector Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	150 1.76	mW mW/°C

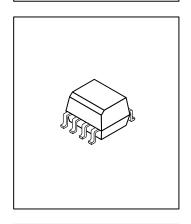
Symbol

Value

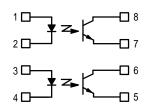
Unit

## **MOCD217**

DUAL CHANNEL SMALL OUTLINE OPTOISOLATOR TRANSISTOR OUTPUT







- 1. ANODE 1
- 2. CATHODE 1
- 3. ANODE 2
- 4. CATHODE 2
- 5. EMITTER 2
- 6. COLLECTOR 2
- 7. EMITTER 1
- 8. COLLECTOR 1



## **MAXIMUM RATINGS** — continued ( $T_{\Lambda} = 25^{\circ}\text{C}$ unless otherwise noted)

	Rating		Symbol	Value		Unit
OTAL DEVICE						
Input–Output Isolation Voltage <sup>(1,2)</sup> (60 Hz, 1.0 sec. duration)			V <sub>ISO</sub>	3000		Vac(rms)
Total Device Power Dissipation @ Total Device Power Device Pow	Г <sub>Д</sub> = 25°С		PD	250 2.94		mW mW/°C
Ambient Operating Temperature Ra	ange(3)		T <sub>A</sub>	-45 to +1	00	°C
Storage Temperature Range(3)			T <sub>stg</sub>	-45 to +1	25	°C
Lead Soldering Temperature (1/16" from case, 10 sec. duratio	n)		_	260		°C
LECTRICAL CHARACTERIST	ICS (T <sub>A</sub> = 25°C unless otherwise	e noted)(4)		-	-	
Characte	ristic	Symbol	Min	Тур(4)	Max	Unit
NPUT LED						
Forward Voltage (I <sub>F</sub> = 1.0 mA)		٧F	_	1.05	1.3	V
Reverse Leakage Current (V <sub>R</sub> = 6.	0 V)	IR	_	0.1	100	μΑ
Capacitance		С	_	18	_	pF
OUTPUT TRANSISTOR			•	•		•
Collector–Emitter Dark Current	$(V_{CE} = 5.0 \text{ V}, T_{A} = 25^{\circ}\text{C})$	ICEO1	_	1.0	50	nA
	$(V_{CE} = 5.0 \text{ V}, T_{A} = 100^{\circ}\text{C})$	I <sub>CEO</sub> 2	<u> </u>	1.0	_	μА
Collector–Emitter Breakdown Volta	ge (I <sub>C</sub> = 100 μA)	V(BR)CEO	30	90	_	V
Emitter-Collector Breakdown Volta	ge (I <sub>E</sub> = 100 μA)	V(BR)ECO	7.0	7.8	_	V
	Collector–Emitter Capacitance (f = 1.0 MHz, V <sub>CF</sub> = 0)					

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Output Collector Current	MOCD217	I <sub>C</sub> (CTR) <sup>(5)</sup>	1.0 (100)	1.3 (130)	_	mA (%)
$(I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$						
Collector–Emitter Saturation Voltage ( $I_C = 100 \mu A$	$A, I_F = 1.0 \text{ mA}$	VCE(sat)	_	0.35	0.4	V
Turn–On Time ( $I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 10 \text{ M}$	00 Ω)	ton		7.5	_	μs
Turn–Off Time ( $I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 10 \text{ M}$	00 Ω)	t <sub>off</sub>	_	5.7	_	μs
Rise Time (I <sub>C</sub> = 2.0 mA, $V_{CC}$ = 10 V, $R_L$ = 100 $\Omega$	)	t <sub>r</sub>	_	3.2	_	μs
Fall Time (I <sub>C</sub> = 2.0 mA, $V_{CC}$ = 10 V, $R_L$ = 100 $\Omega$ )		t <sub>f</sub>	_	4.7	_	μs
Input-Output Isolation Voltage (f = 60 Hz, t = 1.0	sec.) <sup>(1,2)</sup>	VISO	3000	_	_	Vac(rms)
Isolation Resistance (V <sub>I–O</sub> = 500 V) <sup>(2)</sup>		RISO	10 <sup>11</sup>	_	_	Ω
Isolation Capacitance ( $V_{I-O} = 0$ , $f = 1.0 \text{ MHz}$ )(2)		C <sub>ISO</sub>	_	0.2	_	pF

<sup>1.</sup> Input–Output Isolation Voltage,  $V_{\mbox{\scriptsize ISO}}$ , is an internal device dielectric breakdown rating.

<sup>2.</sup> For this test, pins 1, 2, 3 and 4 are common, and pins 5, 6, 7 and 8 are common.

<sup>3.</sup> Refer to Quality and Reliability Section in Opto Data Book for information on test conditions.

<sup>4.</sup> Always design to the specified minimum/maximum electrical limits (where applicable).

<sup>5.</sup> Current Transfer Ratio (CTR) = I<sub>C</sub>/I<sub>F</sub> x 100%.



#### TYPICAL CHARACTERISTICS

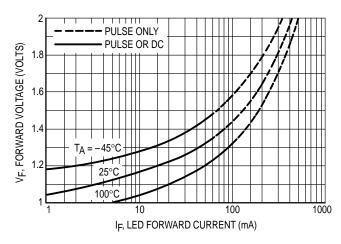


Figure 1. LED Forward Voltage versus Forward Current

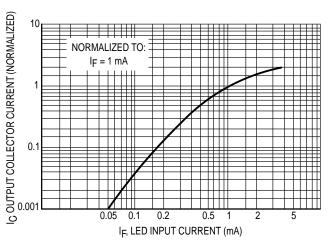


Figure 2. Output Current versus Input Current

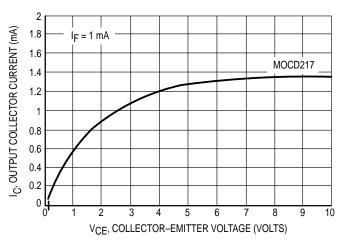


Figure 3. Output Current versus Collector–Emitter Voltage

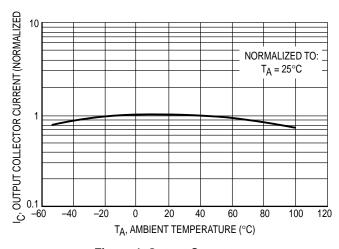


Figure 4. Output Current versus Ambient Temperature

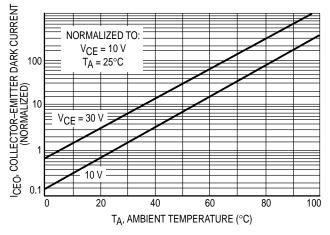


Figure 5. Dark Current versus Ambient Temperature

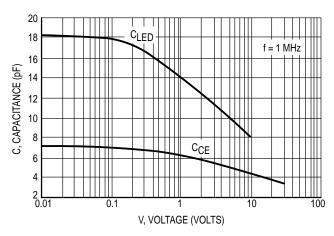
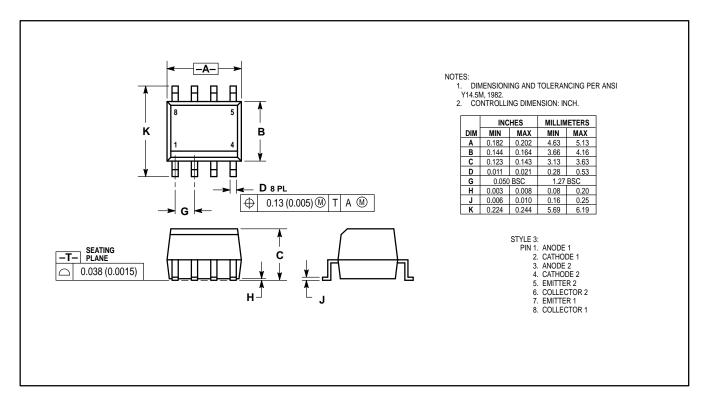


Figure 6. Capacitance versus Voltage



#### **PACKAGE DIMENSIONS**





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recognized - File #E90700, Volume 2

#### Ordering information

The following options can be ordered with this part:

Option	Order Entry Identifier	Description
R1	R1	Surface-Mount Lead Bend Tape and Reel (500-pc reel)
R2	R2	Surface-Mount Lead Bend Tape and Reel (2500-pc reel)

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Product status/pricing/packaging

Product	<b>Product status</b>	Pricing*	Package type	Leads	Packing method
MOCD217-M	Full Production	\$0.422	SOIC	8	RAIL
MOCD217R1-M	Full Production	\$0.431	SOIC	8	TAPE REEL
MOCD217R2-M	Full Production	\$0.431	SOIC	8	TAPE REEL

<sup>\* 1,000</sup> piece Budgetary Pricing

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Safety agency certificates

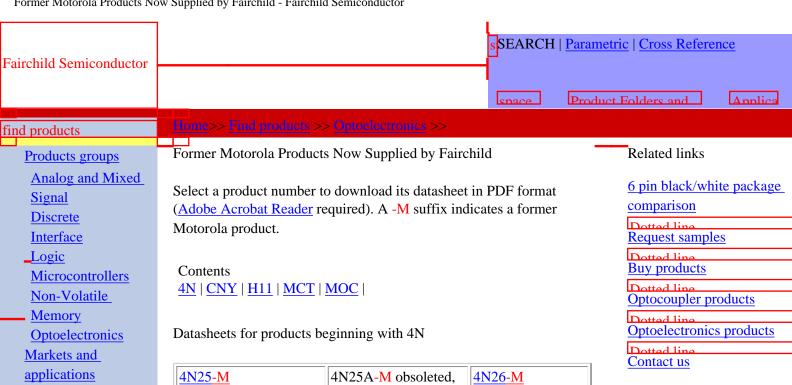
Cetificate	Agency		
<u>136616</u> (161 K)	VDE	VDE Pruf-und Zertifizierungsinstitut	
E90700, Vol. 2 (254 K)	UL	Underwriters Laboratories Inc.	

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4N25-M	4N25A-M obsoleted, no replacement	4N26-M
4N27-M	4N28-M	4N29-M replaced by 4N29
4N29A-M replaced by 4N29	4N30-M replaced by 4N30	4N31-M replaced by 4N31
4N32-M replaced by 4N32	4N33-M replaced by 4N33	4N35-M
4N36-M	4N37-M	4N38-M replaced by 4N38
4N38A-M replaced by 4N38		

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<u>H11A1-M</u>	H11AA1-M replaced by H11AA1	H11AA2-M replaced by H11AA2	

H11AA3-M replaced by H11AA3	H11AA4-M replaced by H11AA4	<u>H11AV1-M</u>
H11AV1A-M	H11AV2-M	H11AV2A-M
H11B1-M replaced by H11B1	H11B3-M replaced by H11B3	H11D1-M replaced by H11D1
H11D2-M replaced by H11D2	H11G1-M replaced by H11G1	H11G2-M replaced by H11G2
H11G3-M replaced by H11G3	H11L1-M	H11L2-M
<u>H11L3-M</u>		

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## Datasheets for products beginning with MCT

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## Datasheets for products beginning with MOC

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<u>MOC208-M</u>	<u>MOC211-M</u>	MOC212-M
<u>MOC213-M</u>	MOC215-M	MOC216-M
<u>MOC217-M</u>	MOC223-M	MOC256-M
MOC3010-M	MOC3011-M	MOC3012-M
MOC3020-M	MOC3021-M	MOC3022-M
MOC3023-M	MOC3031-M	MOC3032-M
MOC3033-M	MOC3041-M	MOC3042-M
MOC3043-M	MOC3051-M	MOC3052-M
MOC3061-M	MOC3062-M	MOC3063-M
MOC3081-M	MOC3081-M	MOC3083-M
MOC3162-M	MOC3163-M	MOC5007-M
MOC5008-M	MOC5009-M	MOC8030-M replaced by MOC8030

Former Motorola Products Now Supplied by Fairchild - Fairchild Semiconductor

MOC8050-M replaced by MOC8050	MOC8080-M replaced by MOC8080	MOC8100-M
MOC8204-M replaced by MOC8204	MOCD207-M	MOCD208-M
MOCD211-M	MOCD213-M	MOCD217-M
MOCD223-M		

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